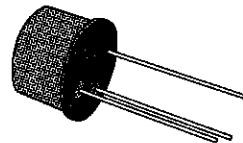


HIGH SPEED SATURATED SWITCHES

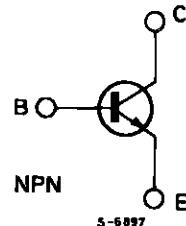
DESCRIPTION

The 2N3013 is a silicon planar epitaxial NPN transistor in Jedec TO-18 metal case intended for high speed low saturation switching application up to 300 mA.



TO-18

INTERNAL SCHEMATIC DIAGRAM



ABSOLUTE MAXIMUM RATINGS

Symbol	Parameter	Value	Unit
V_{CBO}	Collector-base Voltage ($I_E = 0$)	40	V
V_{CES}	Collector-emitter Voltage ($V_{BE} = 0$)	40	V
V_{CEO}	Collector-emitter Voltage ($I_B = 0$)	15	V
V_{EBO}	Emitter-base Voltage ($I_C = 0$)	5	V
I_C	Collector Current	200	mA
I_C	Collector Peak Current ($t < 10 \mu\text{s}$)	500	mA
P_{tot}	Total Power Dissipation at $T_{amb} < 25^\circ\text{C}$ at $T_{case} < 25^\circ\text{C}$ at $T_{case} < 100^\circ\text{C}$	360 1200 680	mW mW mW
T_{stg}	Storage Temperature	-55 to 200	°C
T_j	Max. Operating Junction Temperature	200	°C

THERMAL DATA

$R_{th\ j\text{-case}}$	Thermal Resistance Junction-case	Max	146	$^{\circ}\text{C/W}$
$R_{th\ j\text{-amb}}$	Thermal Resistance Junction-ambient	Max	486	$^{\circ}\text{C/W}$

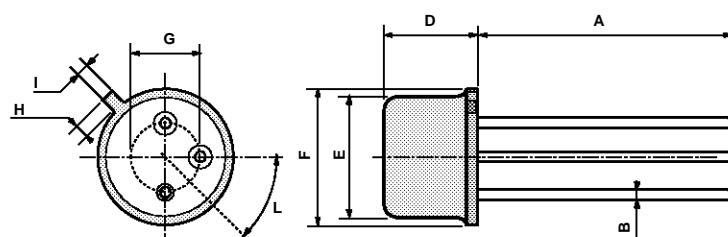
ELECTRICAL CHARACTERISTICS ($T_{amb} = 25^{\circ}\text{C}$ unless otherwise specified)

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
I_{CES}	Collector Cutoff Current ($V_{BE} = 0$)	$V_{CE} = 20\text{ V}$ $V_{CE} = 20\text{ V}$ $T_{amb} = 125^{\circ}\text{C}$			300 40	nA μA
$V_{(BR)CBO}$	Collector-base Breakdown Voltage	$I_C = 100\text{ }\mu\text{A}$ $I_E = 0$	40			V
$V_{(BR)CEO}^*$	Collector-emitter Breakdown Voltage	$I_C = 10\text{ mA}$ $I_B = 0$	15			V
$V_{(BR)EBO}$	Emitter-base Breakdown Voltage	$I_E = 100\text{ }\mu\text{A}$ $I_C = 0$	5			V
h_{FE}^*	DC Current Gain	$V_{CE} = 0.4\text{ V}$ $I_C = 30\text{ mA}$ $V_{CE} = 0.5\text{ V}$ $I_C = 100\text{ mA}$ $V_{CE} = 1\text{ V}$ $I_C = 300\text{ mA}$ $V_{CE} = 0.4\text{ V}$ $I_C = 30\text{ mA}$ $T_{amb} = 55^{\circ}\text{C}$	30 25 15 12		120	
$V_{CE(sat)}^*$	Collector-emitter Saturation Voltage	$I_C = 30\text{ mA}$ $I_B = 3\text{ mA}$ $I_C = 100\text{ mA}$ $I_B = 10\text{ mA}$ $I_C = 300\text{ mA}$ $I_B = 30\text{ mA}$ $I_C = 30\text{ mA}$ $I_B = 3\text{ mA}$ $T_{amb} = 125^{\circ}\text{C}$			0.18 0.28 0.50 0.25	V V V V
$V_{BE(sat)}^*$	Base-emitter Saturation Voltage	$I_C = 30\text{ mA}$ $I_B = 3\text{ mA}$ $I_C = 100\text{ mA}$ $I_B = 10\text{ mA}$ $I_C = 300\text{ mA}$ $I_B = 30\text{ mA}$	0.75		0.95 1.20 1.70	V V V
f_T	Transition Frequency	$V_{CE} = 10\text{ V}$ $I_C = 30\text{ mA}$ $f = 100\text{ MHz}$	350			MHz
C_{CBO}	Collector-base Capacitance	$V_{CB} = 5\text{ V}$; $I_E = 0$ $f = 1\text{ MHz}$			5	pF
C_{EBO}	Emitter-base Capacitance	$V_{EB} = 0.5\text{ V}$; $I_C = 0$ $f = 1\text{ MHz}$			8	pF
t_{on}	Turn-on Time	$V_{CC} = 15\text{ V}$ $I_C = 300\text{ mA}$ $I_{B1} = 30\text{ mA}$			15	ns
t_{off}	Turn-off Time	$V_{CC} = 15\text{ V}$ $I_C = 300\text{ mA}$ $I_{B1} = -I_{B2} = 30\text{ mA}$			25	ns
t_s	Storage Time	$V_{CC} = 10\text{ V}$ $I_C = 10\text{ mA}$ $I_{B1} = -I_{B2} = 10\text{ mA}$			18	ns

* Pulsed : pulse duration = 300 μs , duty cycle = 1.5 %.

TO39 MECHANICAL DATA

DIM.	mm			inch		
	MIN.	TYP.	MAX.	MIN.	TYP.	MAX.
A	12.7			0.500		
B			0.49			0.019
D			6.6			0.260
E			8.5			0.334
F			9.4			0.370
G	5.08			0.200		
H			1.2			0.047
I			0.9			0.035
L	45° (typ.)					



P008B

Information furnished is believed to be accurate and reliable. However, SGS-THOMSON Microelectronics assumes no responsibility for the consequences of use of such information nor for any infringement of patents or other rights of third parties which may result from its use. No license is granted by implication or otherwise under any patent or patent rights of SGS-THOMSON Microelectronics. Specifications mentioned in this publication are subject to change without notice. This publication supersedes and replaces all information previously supplied. SGS-THOMSON Microelectronics products are not authorized for use as critical components in life support devices or systems without express written approval of SGS-THOMSON Microelectronics.

© 1994 SGS-THOMSON Microelectronics - All Rights Reserved

SGS-THOMSON Microelectronics GROUP OF COMPANIES
Australia - Brazil - France - Germany - Hong Kong - Italy - Japan - Korea - Malaysia - Malta - Morocco - The Netherlands -
Singapore - Spain - Sweden - Switzerland - Taiwan - Thailand - United Kingdom - U.S.A